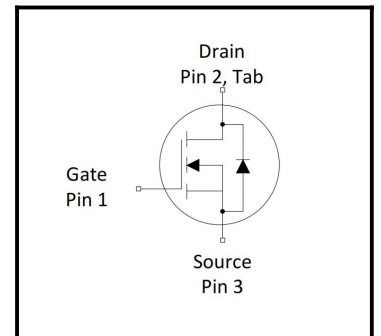
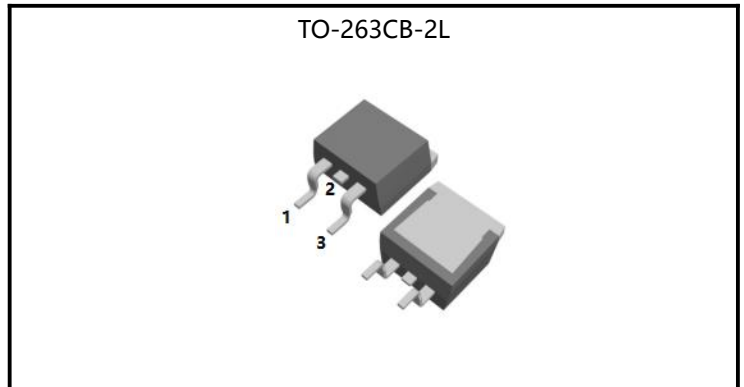


## MOSFET

200 Amps,40 Volts N-CHANNEL MOSFET

### FEATURE

- ◆ Low gate charge
- ◆ Low Ciss
- ◆ Fast switching
- ◆ 100% avalanche tested
- ◆ Improved dv/dt capability
- ◆ RoHS 2.0 Compliant



Parameter	Values	Unit
Bvdss	40	V
Id	200	A
Rdson(max)	3	mΩ

Ordering Code	Marking	Package	Packaging
PW030N04CB	PW030N04CB	TO-263CB-2L	Tape and reel

## Absolute Maximum Ratings( $T_C=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Drain-Source Voltage	$V_{DSS}$	-	-	40	V	-
Gate-Source Voltage	$V_{GS}$	-20	-	20	V	-
Continuous Drain Current(Package Limited)	$I_D$	-	-	200	A	$T_C=25^{\circ}\text{C}$
		-	-	160	A	$T_C=100^{\circ}\text{C}$
Pulsed Drain Current(Note1)	$I_{DM}$	-	-	800	A	-
Single Pulse Avalanche Energy	$E_{AS}$	-	-	1200	mJ	$L=0.5\text{mH}, V_D=32\text{V}, T_C=25^{\circ}\text{C}$
Maximum Power Dissipation	$P_D$	-	-	250	W	$T_C=25^{\circ}\text{C}$
Reverse Diode $dV/dt$ (Note2)	$dv/dt$	-	-	5	V/ns	-
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55	-	150	$^{\circ}\text{C}$	-
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	$T_L$	-	-	260	$^{\circ}\text{C}$	-

## Thermal Characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Thermal resistance , Channel to Case	$R_{th(ch-c)}$	-	0.5	-	$^{\circ}\text{C}/\text{W}$	-
Thermal resistance , Channel to Ambient	$R_{th(ch-a)}$	-	62	-		-

## Electrical Characteristics ( $T_C=25^{\circ}\text{C}$ , unless otherwise noted)

### Static characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Drain-Source Breakdown Voltage	$BV_{DSS}$	40	-	-	V	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	-	-	1.0	$\mu\text{A}$	$V_{DS}=40\text{V}, V_{GS}=0\text{V}$
Gate-Body Leakage Current, Forward	$I_{GSSF}$	-	-	100	nA	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$
Gate-Body Leakage Current, Reverse	$I_{GSSR}$	-	-	-100	nA	$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	2.0	-	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
Drain-Source On-State Resistance	$R_{DS(on)}$	-	2.2	3	$\text{m}\Omega$	$V_{GS}=10\text{V}, I_D=20\text{A}$
Gate Resistance	$R_g$	-	2.1	-	$\Omega$	$V_{GS}=0\text{V}, V_{DS}$ Open, $f=1\text{MHz}$
Forward Transconductance	$g_{fs}$	-	221	-	S	$V_{DS}=10\text{V}, I_D=20\text{A}$

## Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Input Capacitance	$C_{iss}$	-	4840	-	pF	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$
Output Capacitance	$C_{oss}$	-	680	-	pF	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$
Reverse Transfer Capacitance	$C_{rss}$	-	430	-	pF	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$
Turn-On Delay Time	$t_{d(on)}$	-	21	-	ns	$V_{DD}=20V, R_G=2.5\Omega, V_{GS}=10V, I_D=20A$
Turn-On Rise Time	$t_r$	-	22	-	ns	$V_{DD}=20V, R_G=2.5\Omega, V_{GS}=10V, I_D=20A$
Turn-Off Delay Time	$t_{d(off)}$	-	53	-	ns	$V_{DD}=20V, R_G=2.5\Omega, V_{GS}=10V, I_D=20A$
Turn-Off Fall Time	$t_f$	-	21	-	ns	$V_{DD}=20V, R_G=2.5\Omega, V_{GS}=10V, I_D=20A$

## Gate charge characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Total Gate Charge	$Q_g$	-	95	-	nC	$V_{DS}=20V, I_D=20A, V_{GS}=10V$
Gate-Source Charge	$Q_{gs}$	-	27	-	nC	$V_{DS}=20V, I_D=20A, V_{GS}=10V$
Gate-Drain Charge	$Q_{gd}$	-	28	-	nC	$V_{DS}=20V, I_D=20A, V_{GS}=10V$

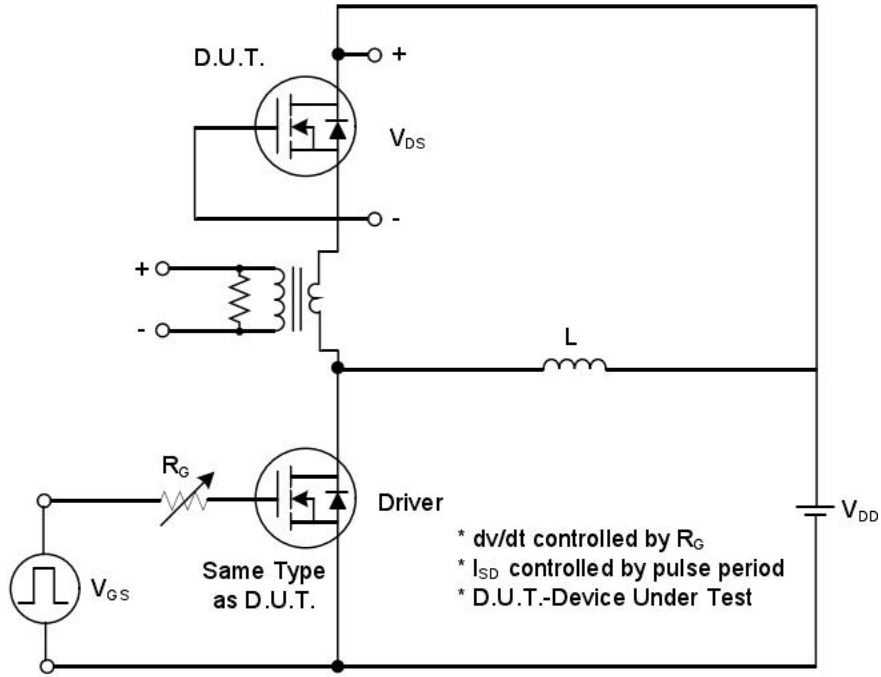
## Reverse diode

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Continuous Diode Forward Current	$I_S$	-	-	200	A	-
Pulsed Diode Forward Current	$I_{SM}$	-	-	800	A	-
Diode Forward Voltage	$V_{SD}$	-	0.90	1.2	V	$I_S=20A, V_{GS}=0V$
Reverse Recovery Time	$t_{rr}$	-	46	-	ns	$V_{GS}=0V, I_F=20A$
Reverse Recovery Charge	$Q_{rr}$	-	19	-	nC	$di/dt=100A/\mu s, (Note2)$

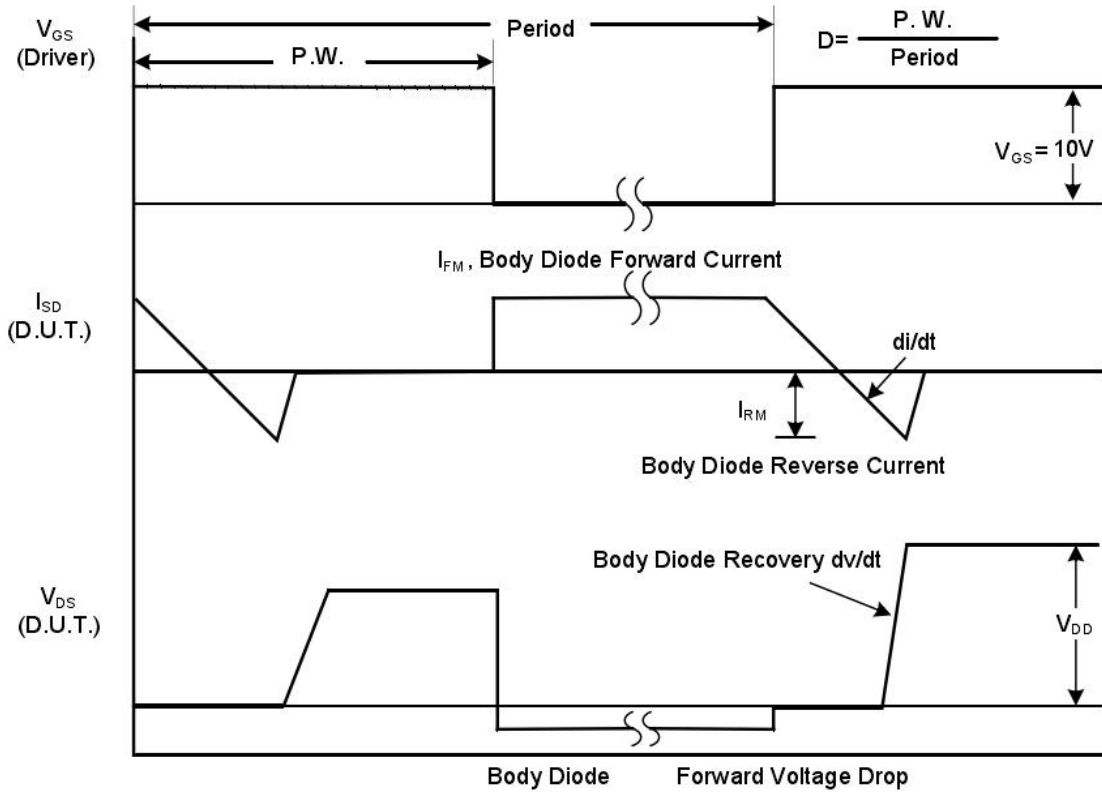
## Notes

1. Repetitive Rating:pulse width limited by maximum junction temperature.
2. Pulse width $\leq 300\mu s$ ,duty cycle $\leq 2\%$ .

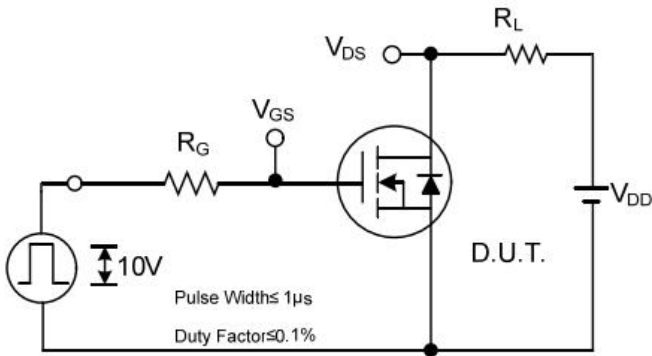
RATING AND CHARACTERISTIC CURVES



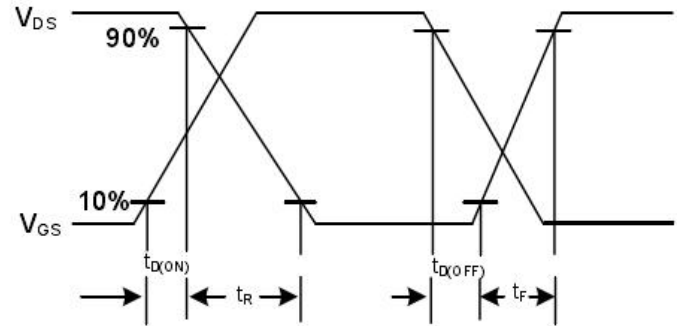
Peak Diode Recovery dv/dt Test Circuit



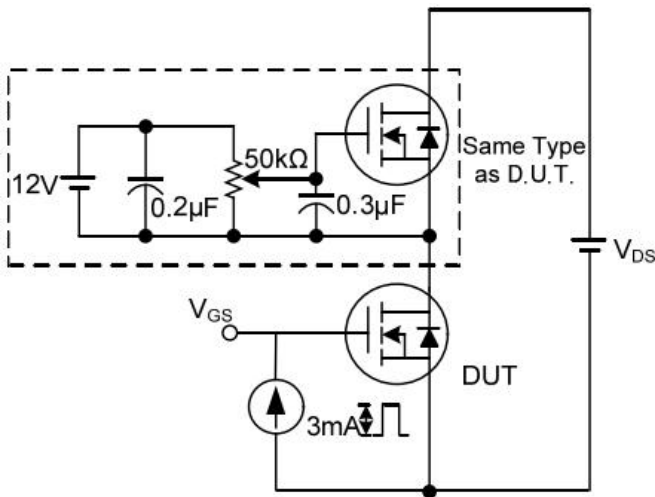
Peak Diode Recovery dv/dt Waveforms



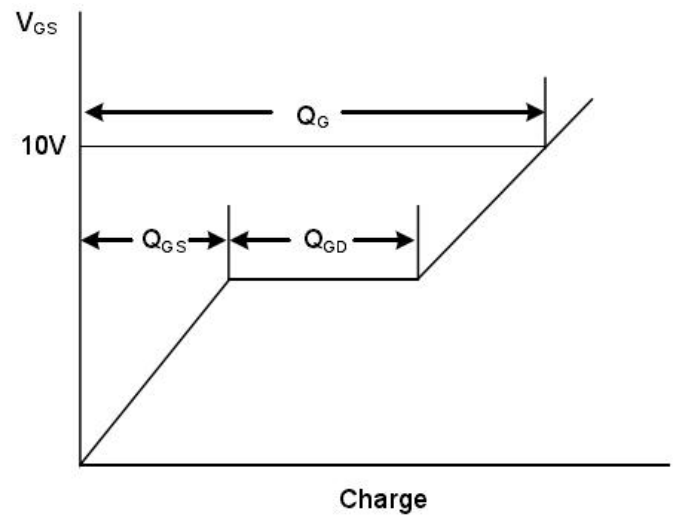
Switching Test Circuit



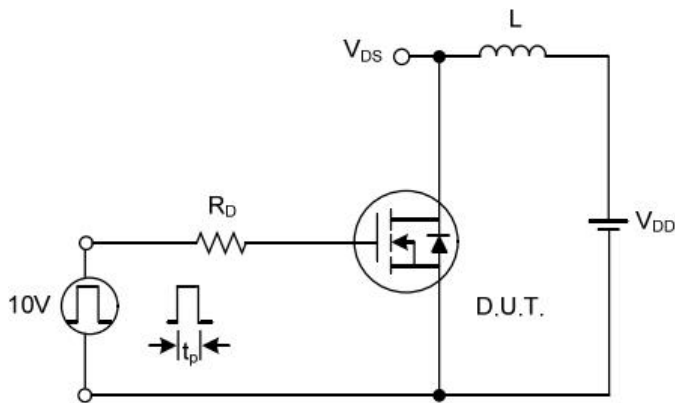
Switching Waveforms



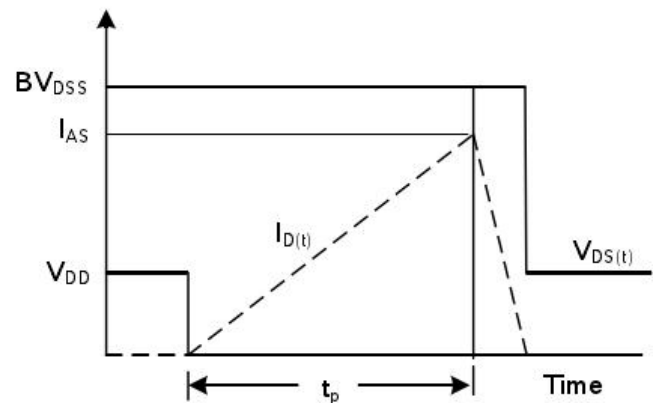
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



## RATING AND CHARACTERISTIC CURVES

Figure.1 Typical Output Characteristics

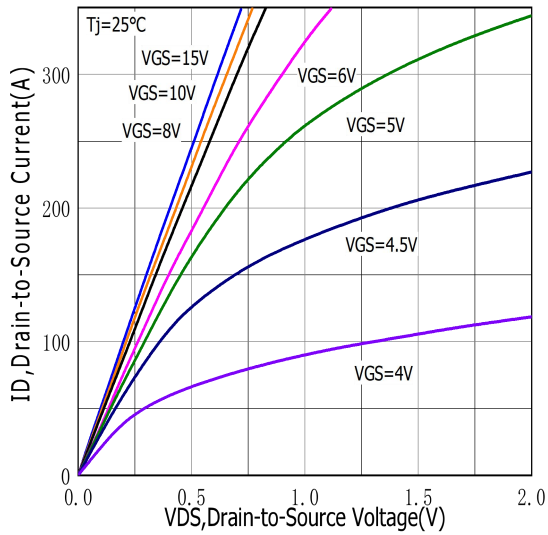


Figure.2 Typical Gate Charge vs Gate to Source Voltage

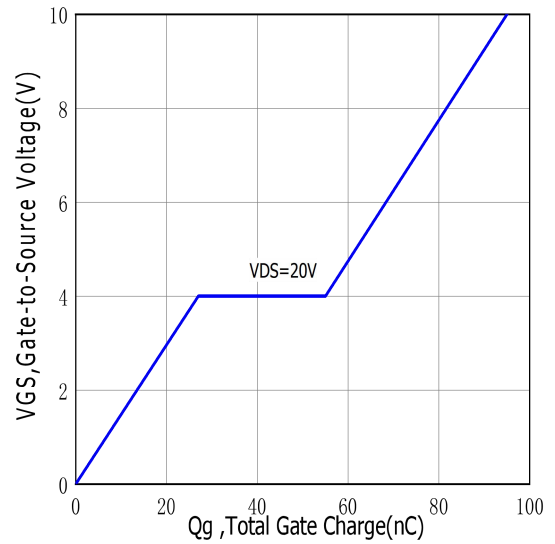


Figure.3 Typical Body Diode Transfer Characteristics

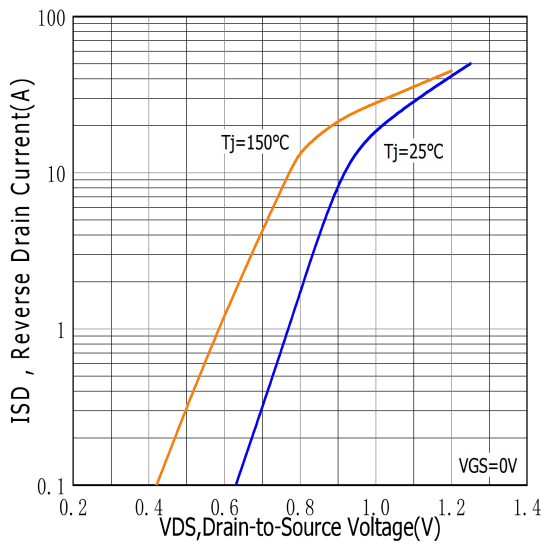
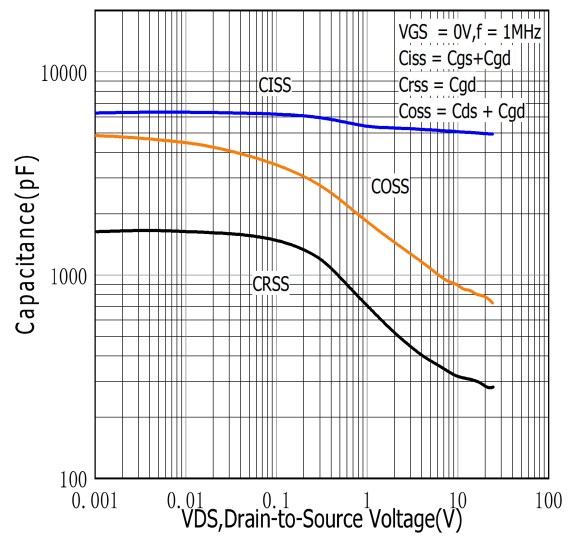
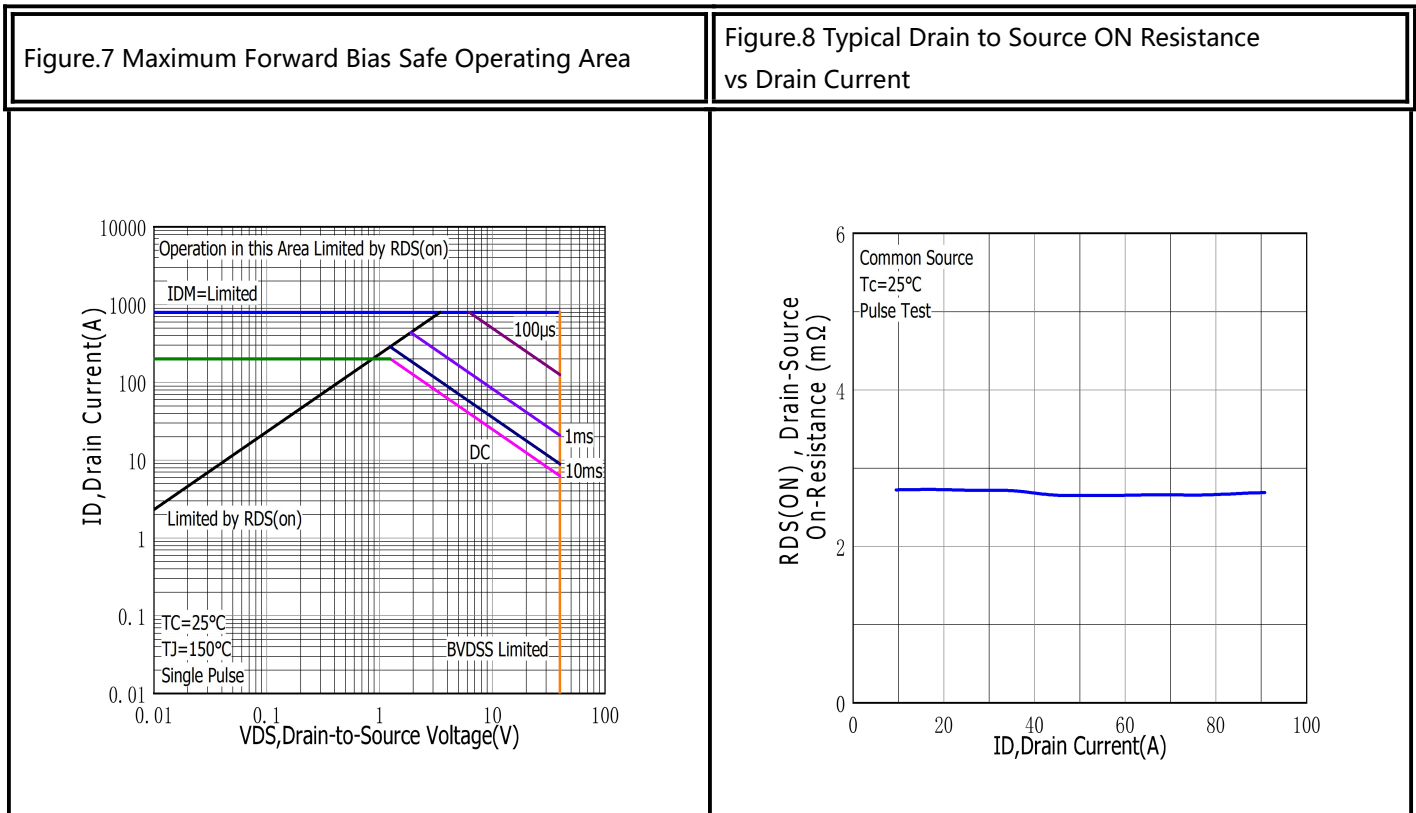
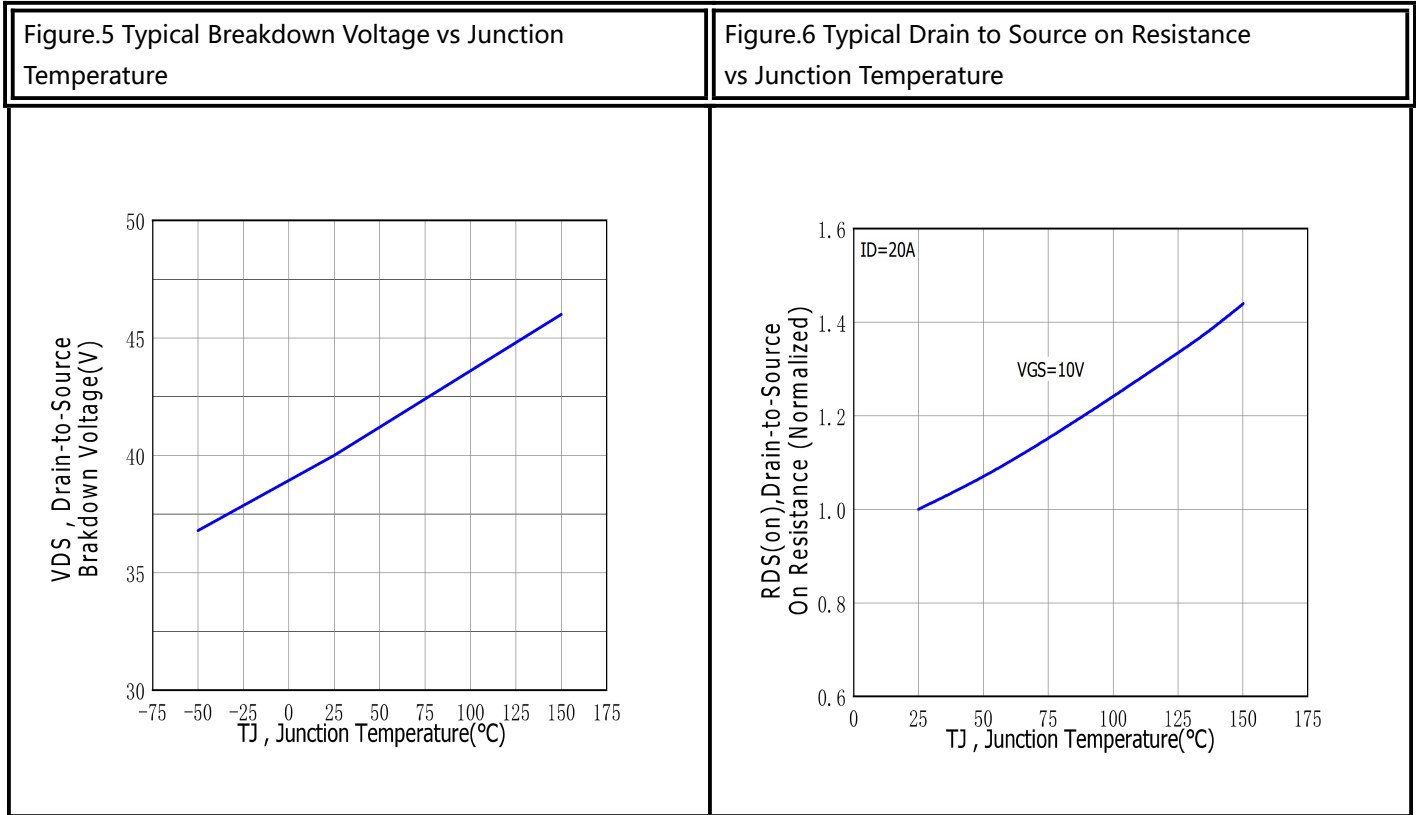


Figure.4 Typical Capacitance vs Drain to Source Voltage





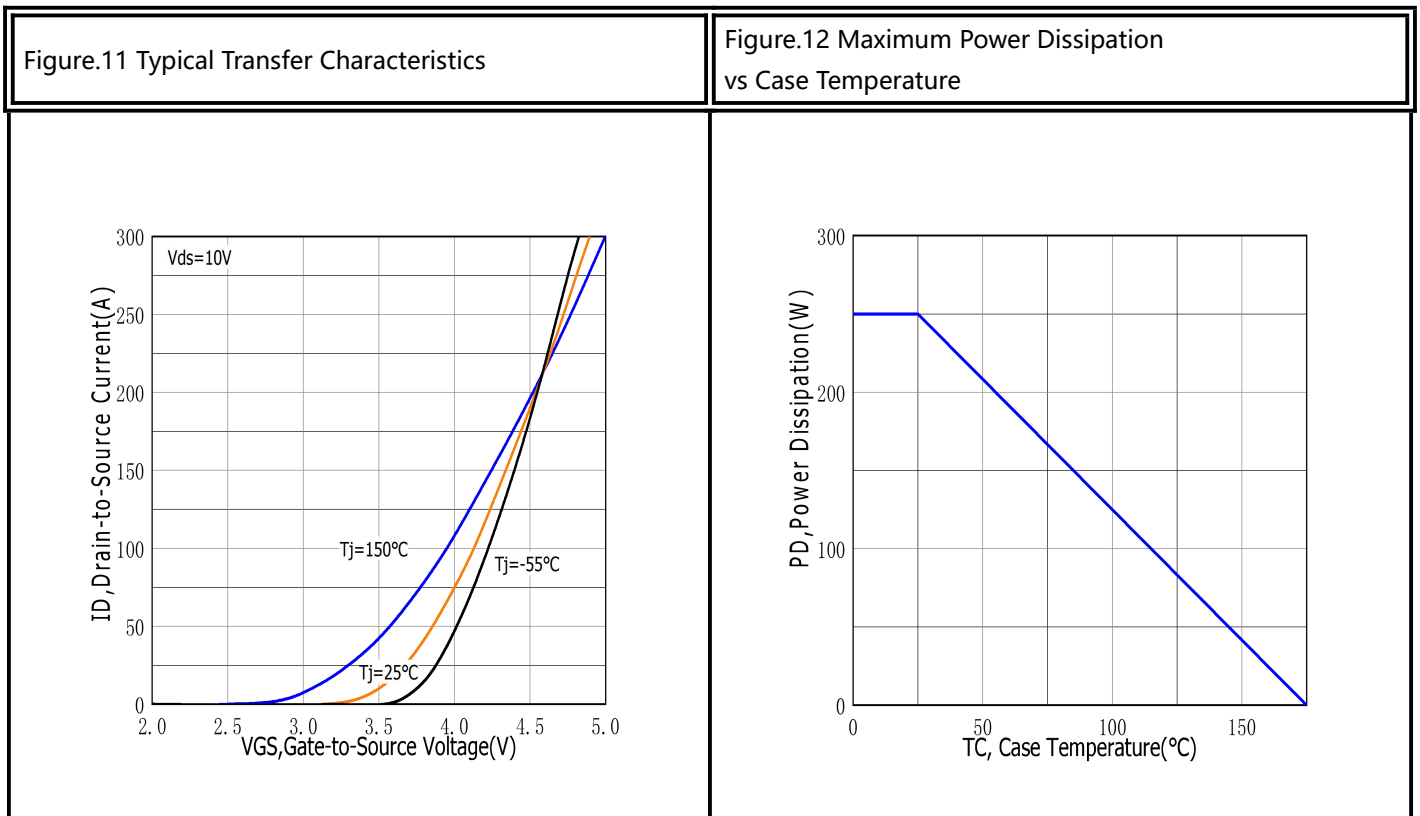
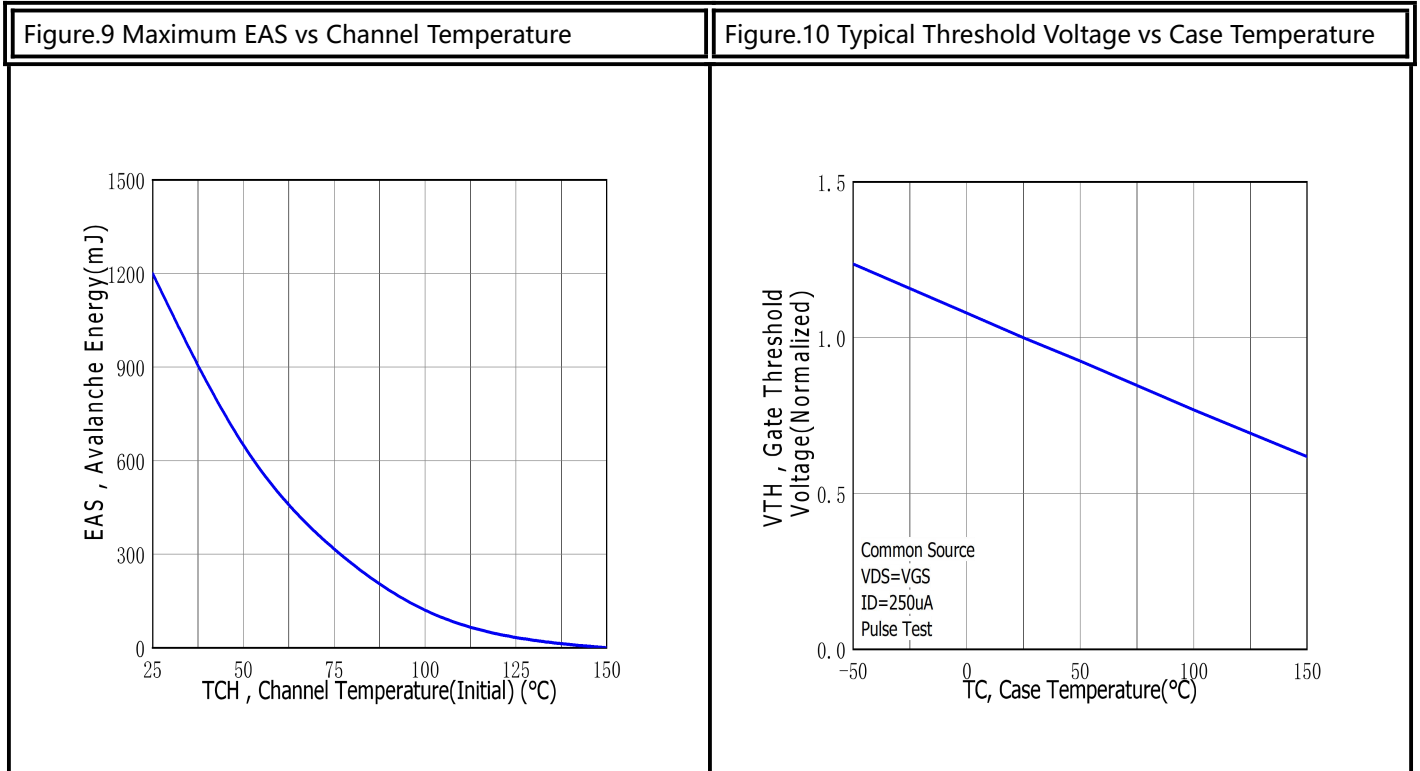
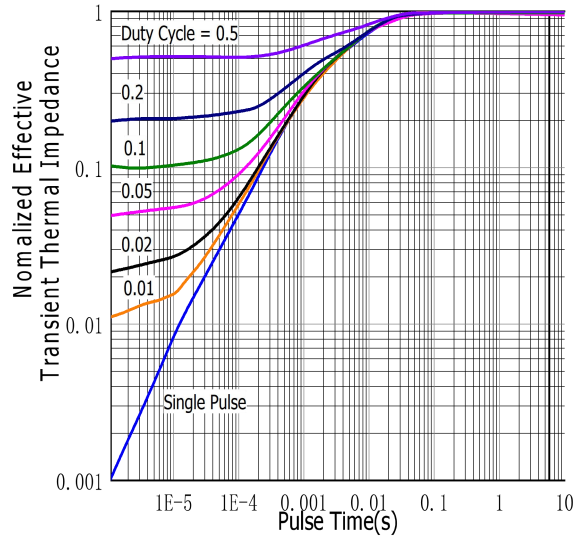


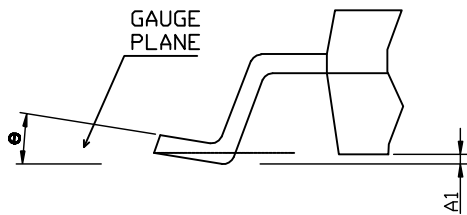
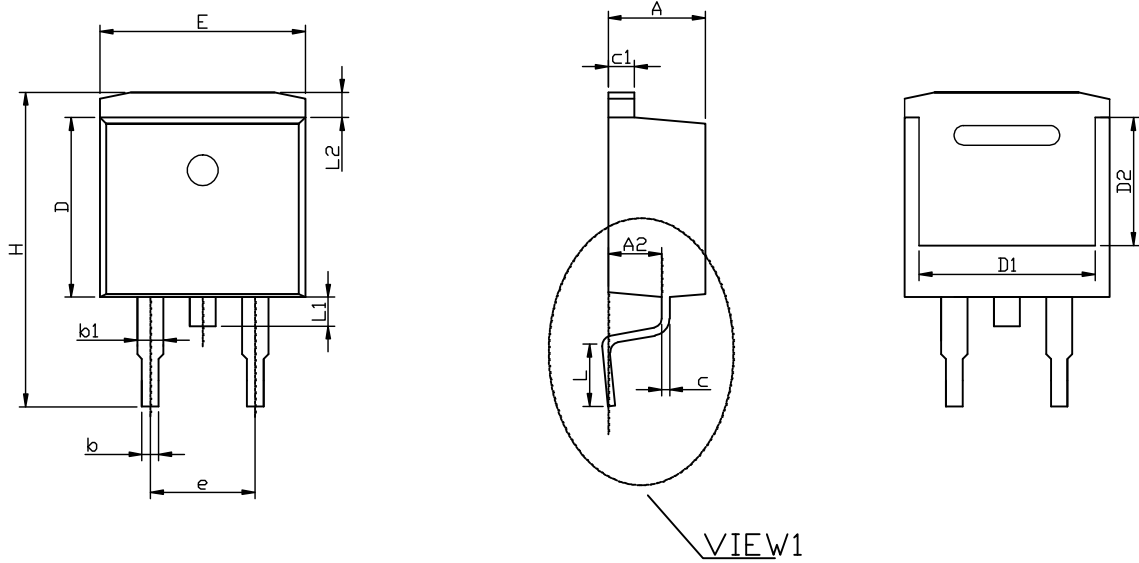




Figure.13 Maximum Effective Thermal Impedance , Junction to Case

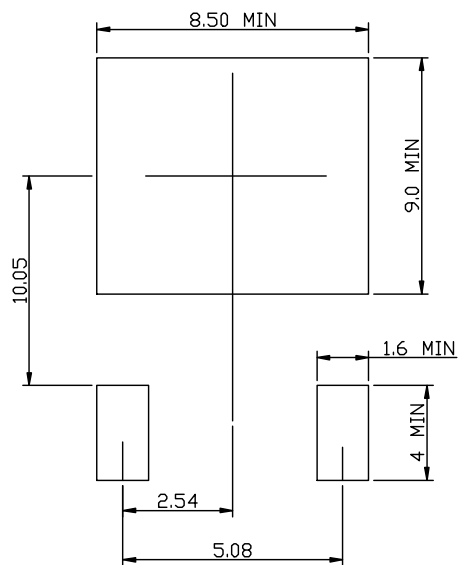


# TO-263CB-2L PACKAGE OUTLINE



VIEW1

## RECOMMENDED LAND PATTERN



	MIN	NOM	MAX
A	4.40	4.60	4.80
A1	0.05	0.15	0.30
A2	2.25	2.40	2.55
b	0.72	0.82	0.92
b1	1.12	1.27	1.42
c	0.40	0.50	0.60
c1	1.20	1.30	1.40
D	8.80	9.10	9.40
D1	7.75	7.95	8.15
D2	6.55	6.75	6.95
E	9.65	10.00	10.35
e		5.08BCS	
H	14.70	15.10	15.60
L	2.30	2.45	2.60
L1	1.20	1.40	1.60
L2	0.95	1.10	1.30
θ	0°	7°	8°

UNIT: mm